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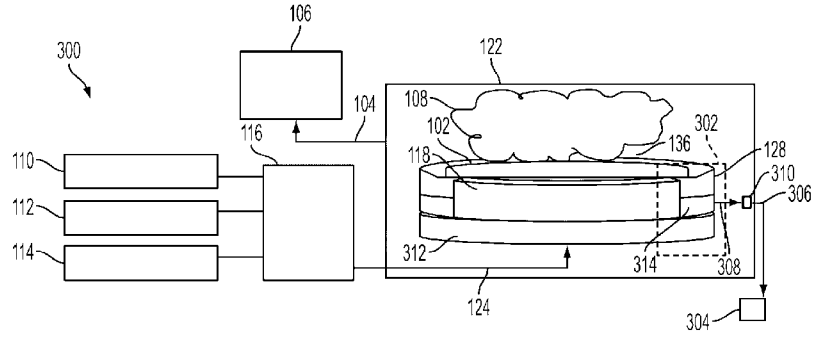
— *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

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— *without international search report and to be republished upon receipt of that report (Rule 48.2(g))*

(54) **Title**: METHOD AND APPARATUS FOR MEASURING WAFER BIAS POTENTIAL

[Fig. 3]



(57) **Abstract**: A device for use in a wafer processing chamber having a plasma forming volume and a hot edge ring. The hot edge ring has a first surface and a second surface. The first surface is in contact with the plasma forming volume. The second surface is not in contact with the plasma forming volume. The device includes a detector operable to contact the second surface of the hot edge ring. The detector can detect a parameter of the hot edge ring and can provide a detected signal based on the detected parameter.

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